Product data sheet

1. General description

Ultrafast power diode in a SOD142 (2-lead TO247) plastic package.

2. Features and benefits

- Fast switching
- Very low on-state loss
- Low leakage current
- · Low thermal resistance

3. Applications

- · Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- · Half-bridge / full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; $T_{mb} \le$ 129 °C; Fig. 1; Fig. 2; Fig. 3	30				A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le$ 129 °C; square-wave pulse	60			А	
I _{FSM} non-repetitive peak forward current		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	290			А	
	$t_p = 8.3 \text{ ms}; T_{j(init)} = 25 \text{ °C}; \text{ sine-wave pulse};$ 330		80		Α		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics			,			
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-		1.18	1.55	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-		0.98	-	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-		42	75	ns
		$I_F = 30 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-		65	-	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-		101	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K — A 001aaa020
2	Α	anode		001aaa020
mb	mb	mounting base; connected to cathod	1 1 2 2 TO-247 (SOD142)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYV30W-600P	TO-247	Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247	SOD142		

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYV30W-600P	BYV30W-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; $T_{mb} \le 129$ °C; Fig. 1; Fig. 2; Fig. 3	30	Α
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 129 °C$; square-wave pulse	60	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	290	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	330	Α
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C

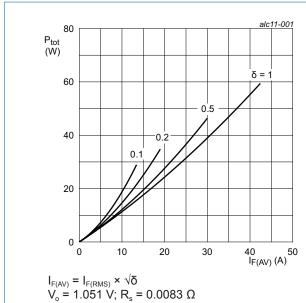
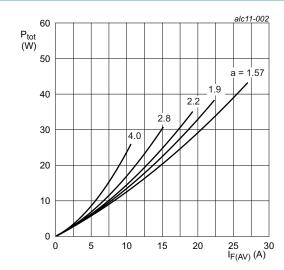
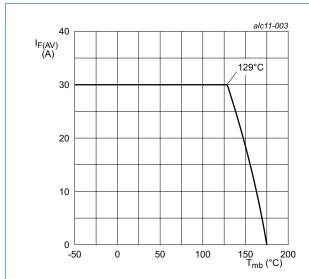


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ Vo = 1.051 V; Rs = 0.0083 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values





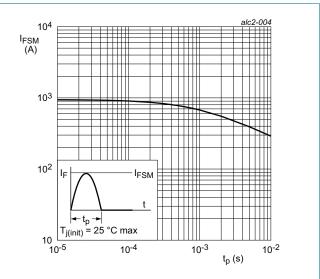


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

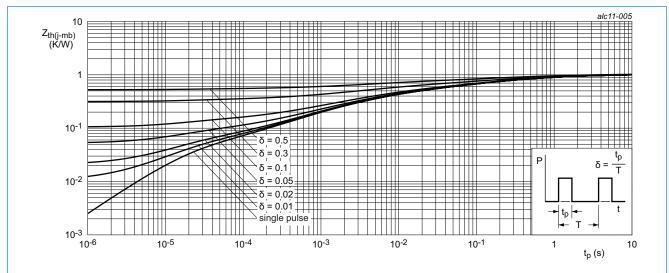
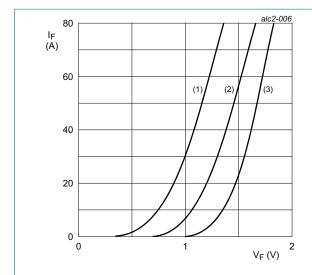


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward current	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.18	1.55	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.98	-	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	2	10	μA
		V _R = 600 V; T _j = 125 °C	-	-	500	μΑ
Dynamic	characteristics			'		
Q _r	reverse charge	$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	272	-	nC
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	775	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	42	75	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	65	-	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	101	-	ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	8.4	-	А
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	15.2	-	Α



 V_o = 1.051 V; R_s = 0.0083 Ω

(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 6. Forward current as a function of forward voltage

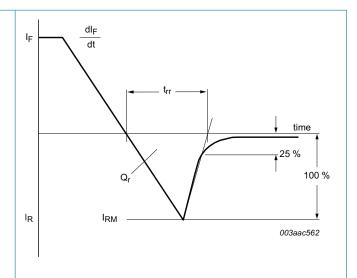


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline

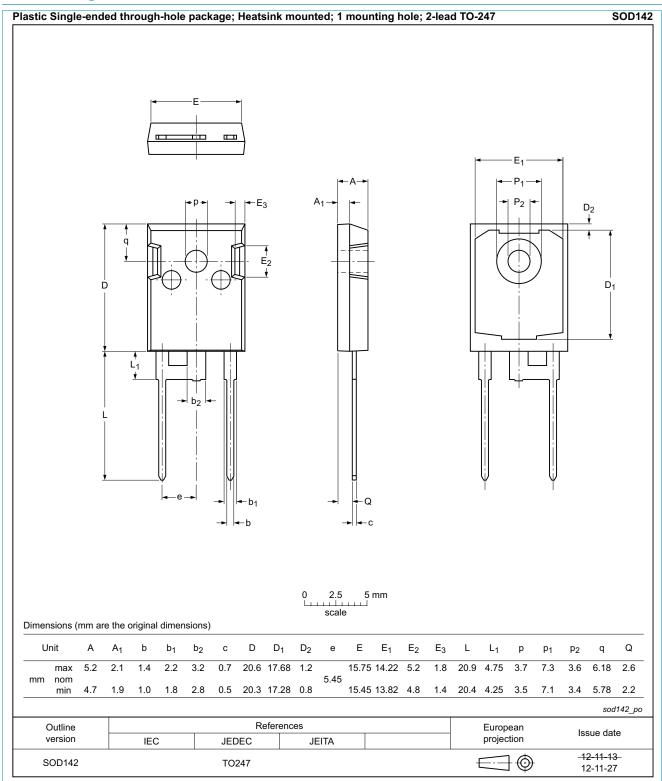


Fig. 8. Package outline SOD142

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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BYV30W-600P

Ultrafast power diode

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